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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Toshihiro ANDO et al.**

Group Art Unit: **1765**

Serial No.: **09/926,188**

Examiner: **Matthew J. SONG**

Filed: **September 20, 2001**

Confirmation No.: **4371**

For: **N-TYPE SEMICONDUCTOR DIAMOND AND METHOD OF ITS
MAKING**

Attorney Docket No.: **011147**

Customer Number: **38834**

SUPPLEMENTAL AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

February 9, 2004

Sir:

In response to the Office Action dated September 15, 2003, and further to Applicant's Response dated December 15, 2003 ("Previous Response"), Applicant submits the following remarks, which begin on page 2 of this paper. The following comments update only the section of the Previous Response entitled, "Claim Rejections under 35 U.S.C. §103". The only change appears in this paper on page 3, lines 16 and 17, wherein the phrase "~~one μ m height~~" is replaced by "**one atomic layer height**". Applicants have highlighted the changed text using boldface type, underlining and strikethrough. Applicants submit that this was the intended text, and is fully consistent with the specification, and particularly with claim 6.